

## MANUFACTURE OF SEMICONDUCTOR DEVICE

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### Abstract of JP2000114173

**PROBLEM TO BE SOLVED:** To realize high-performance semiconductor device by providing the semiconductor film having the crystal property that can be practically regarded as the single crystal and assembling the circuit with a TFT. **SOLUTION:** In this manufacture, following steps are provided, in a first step, heat annealing is performed for the semiconductor film including germanium, and the semiconductor film including a crystal is formed; in a next step, oxidization is performed for the semiconductor film including the crystal; in a next step, laser annealing is performed for the semiconductor film, whose oxidization is performed; and in the last step, furnace annealing is performed for the semiconductor film after laser annealing. The laser annealing is performed under the energy density of 250-5,000 mJ/cm<sup>2</sup>.

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